



Docket: 14467.05

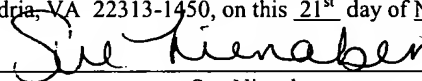
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

First Named Inventor:	John P. Snyder	
Appln. No.:	10/796,514	
Filing Date:	March 9, 2004	Examiner: Kim, Su C.
Title:	Transistor Having High Dielectric Constant Gate Insulating Layer and Source and Drain Forming Schottky Contact with Substrate	Group Art Unit: 2823

RESPONSE AND AMENDMENT UNDER 37 C.F.R. 1.111

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, Virginia 22313-1450

I hereby certify that this document is being sent via First Class U. S. mail addressed to: Mail Stop Amendment, Commissioner for Patents, P. O Box 1450, Alexandria, VA 22313-1450, on this 21st day of November, 2005.


Sue Nienaber

Dear Sir:

In response to the Office Action dated May 20, 2005, please amend the above-identified application as follows:

Claims begin on page 2 of this paper.

Remarks begin on page 15 of this paper.